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ZXT10N50DE6

SuperSOT™

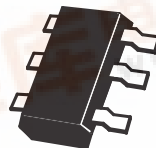
50V NPN SILICON LOW SATURATION SWITCHING TRANSISTOR

SUMMARY

$V_{CE0}=50V$; $R_{SAT}=75m\Omega$; $I_C=3A$

DESCRIPTION

This new 4th generation ultra low saturation transistor utilises the Zetex matrix structure combined with advanced assembly techniques to give extremely low on state losses. This makes it ideal for high efficiency, low voltage switching applications.



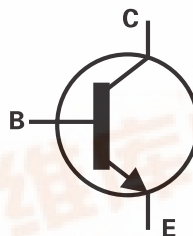
SOT23-6

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage
- h_{FE} characterised up to 12A
- $I_C=3A$ Continuous Collector Current
- SOT23-6 package

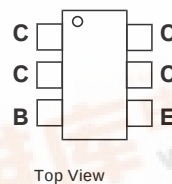
APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Power switches
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXT10N50DE6TA	7	8mm embossed	3000 units
ZXT10N50DE6TC	13	8mm embossed	10000 units



Top View

DEVICE MARKING

619



ZXT10N50DE6

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	6	A
Continuous Collector Current	I_C	3	A
Base Current	I_B	500	mA
Power Dissipation at $T_A=25^{\circ}\text{C}$ (a) Linear Derating Factor	P_D	1.1 8.8	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (b) Linear Derating Factor	P_D	1.7 13.6	W mW/ $^{\circ}\text{C}$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}\text{C}$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	113	$^{\circ}\text{C/W}$
Junction to Ambient (b)	$R_{\theta JA}$	73	$^{\circ}\text{C/W}$

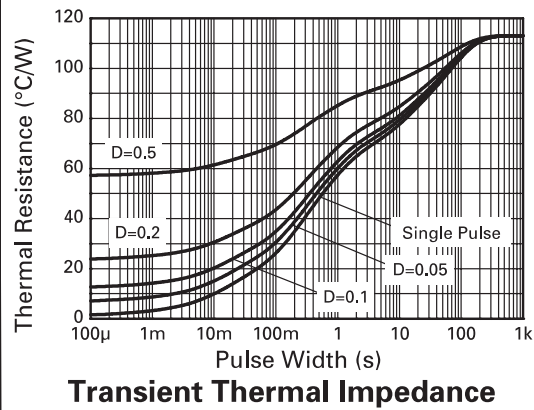
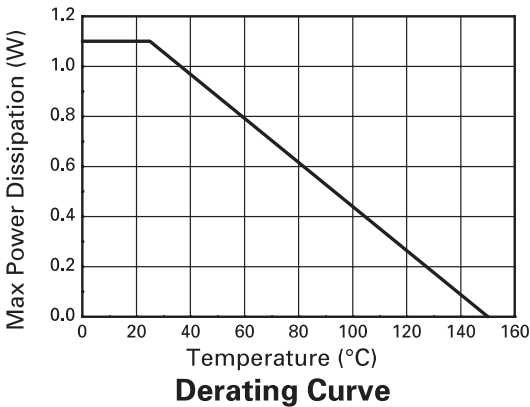
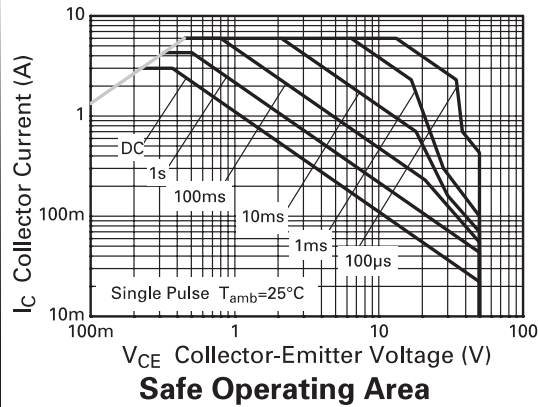
NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

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TYPICAL CHARACTERISTICS



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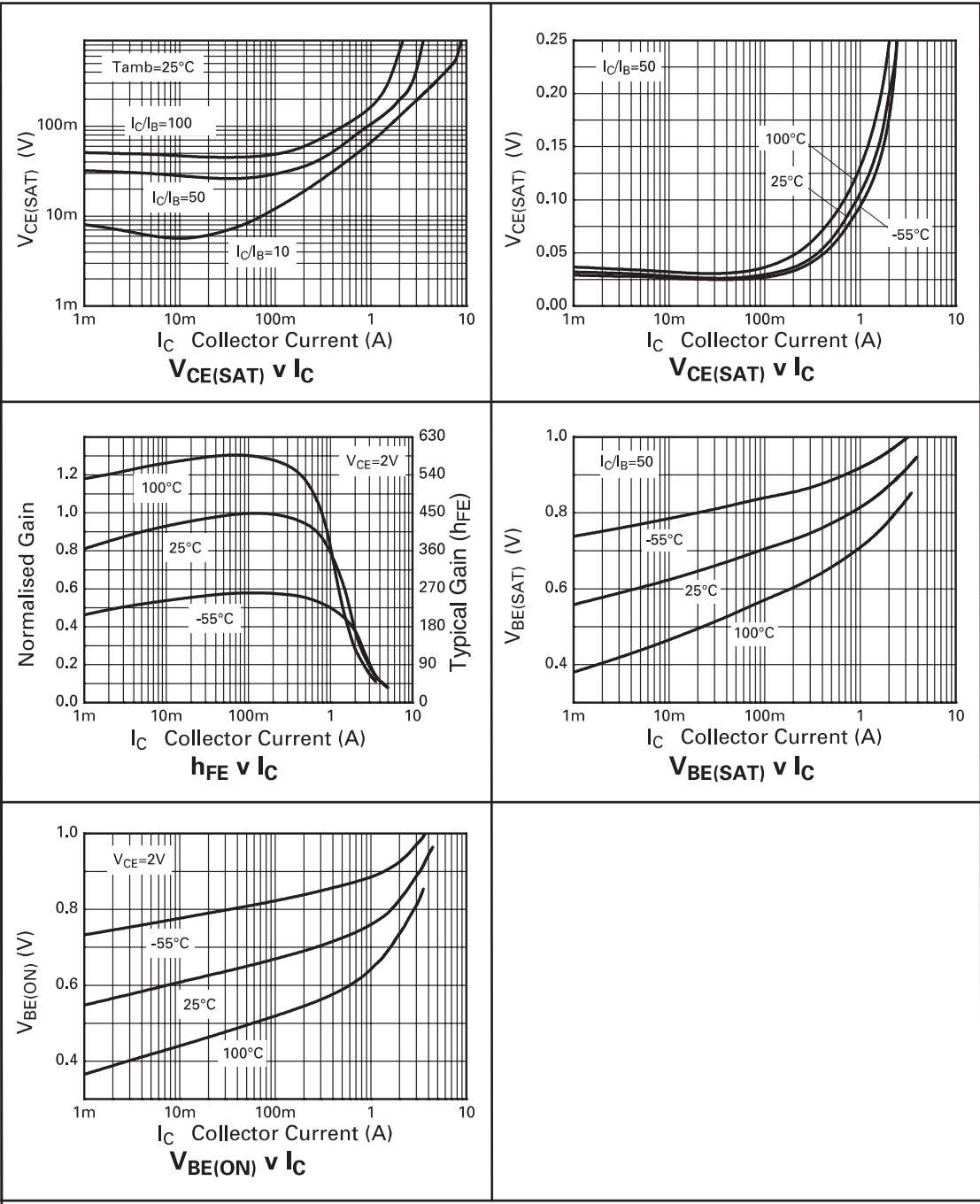
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50	190		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	50	65		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	8.3		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB}=40\text{V}$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			100	nA	$V_{CES}=40\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		14 145 115 225	20 200 200 300	mV mV mV mV	$I_C=0.1\text{A}, I_B=10\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=2\text{A}, I_B=50\text{mA}^*$ $I_C=3\text{A}, I_B=100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.93	1.0	V	$I_C=3\text{A}, I_B=100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.88	0.95	V	$I_C=3\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200 300 200 100	400 450 400 225 40			$I_C=10\text{mA}, V_{CE}=2\text{V}^*$ $I_C=0.2\text{A}, V_{CE}=2\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$ $I_C=2\text{A}, V_{CE}=2\text{V}^*$ $I_C=6\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	100	165		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		12	20	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		170		ns	$V_{CC}=10\text{V}, I_C=1\text{A}$ $I_{B1}=I_{B2}=10\text{mA}$
Turn-Off Time	$t_{(off)}$		750		ns	

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

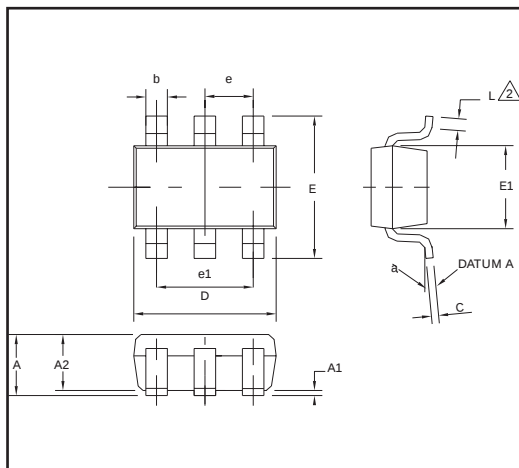
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TYPICAL CHARACTERISTICS

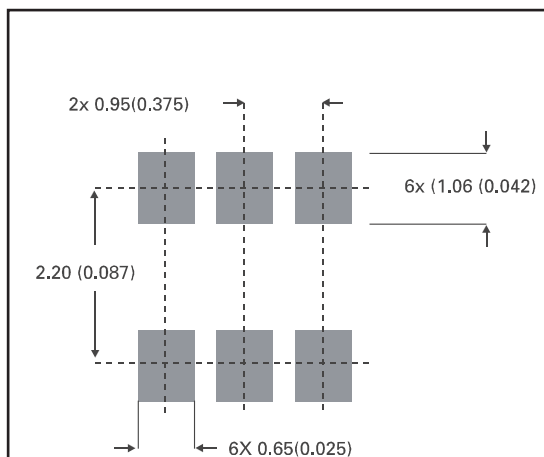


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PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	0.90	1.45	0.35	0.057
A1	0.00	0.15	0	0.006
A2	0.90	1.30	0.035	0.051
b	0.35	0.50	0.014	0.019
C	0.09	0.20	0.0035	0.008
D	2.80	3.00	0.110	0.118
E	2.60	3.00	0.102	0.118
E1	1.50	1.75	0.059	0.069
L	0.10	0.60	0.004	0.002
e	0.95 REF		0.037 REF	
e1	1.90 REF		0.074 REF	
L	0°	10°	0°	10°



Zetex plc.
Fields New Road, Chadderton, Oldham, OL9-8NP, United Kingdom.
Telephone: (44)161 622 4422 (Sales), (44)161 622 4444 (General Enquiries)
Fax: (44)161 622 4420

Zetex GmbH
Streitfeldstraße 19
D-81673 München
Germany
Telefon: (49) 89 45 49 49 0
Fax: (49) 89 45 49 49 49

Zetex Inc.
47 Mall Drive, Unit 4
Commack NY 11725
USA
Telephone: (631) 543-7100
Fax: (631) 864-7630

Zetex (Asia) Ltd.
3701-04 Metroplaza, Tower 1
Hing Fong Road,
Kwai Fong, Hong Kong
Telephone: (852) 26100 611
Fax: (852) 24250 494

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